

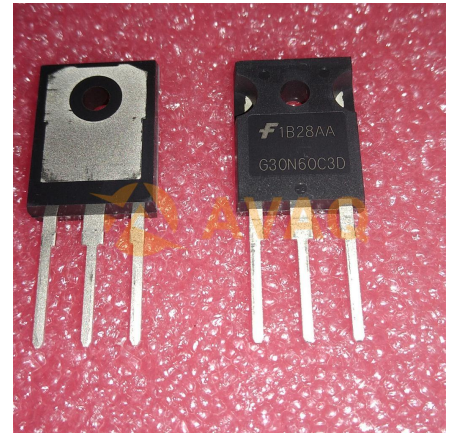
600V, PT IGBT

Manufacturer: ON Semiconductor, LLC

Package/Case: TO-247

Product Type: Thyristors

Lifecycle: Obsolete



Images are for reference only

[Inquiry](#)

General Description

The HGTG30N60C3D is a MOS gated high voltage switching device combining the best features of MOSFETs and bipolar transistors. The device has the high input impedance of a MOSFET and the low on-state conduction loss of a bipolar transistor. The much lower on-state voltage drop varies only moderately between 25°C and 150°C. The IGBT used is the development type TA49051. The diode used in anti-parallel with the IGBT is the development type TA49053. The IGBT is ideal for many high voltage switching applications operating at moderate frequencies where low conduction losses are essential. Formerly Developmental Type TA49014.

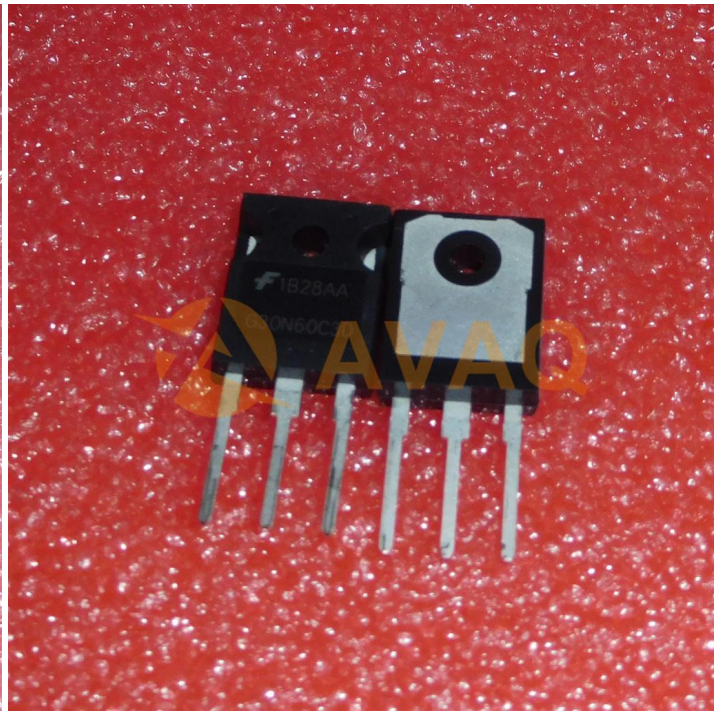
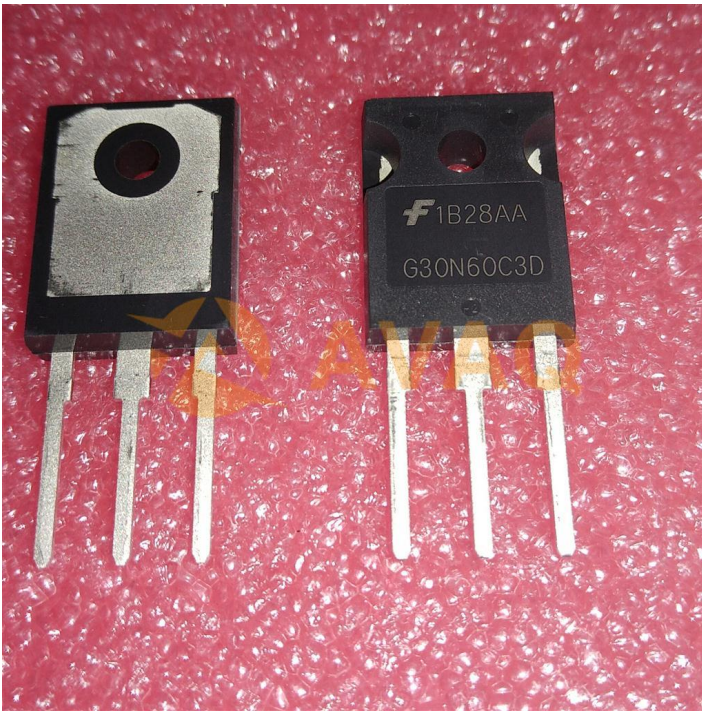
Key Features

C

J

Application

Other Industrial



Recommended For You

HGTG20N60B3D

ON Semiconductor, LLC

TO-247

HGTG11N120CND

ON Semiconductor, LLC

TO-247

HGTG20N60B3

ON Semiconductor, LLC

TO-247

HGTP3N60A4

ON Semiconductor, LLC

TO-220

HGTG11N120CN

ON Semiconductor, LLC

TO-247

HGTG12N60A4D

ON Semiconductor, LLC

TO-247

HGTP7N60C3D

ON Semiconductor, LLC

TO-220

HGTG10N120BND

ON Semiconductor, LLC

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HGTP10N120BN

ON Semiconductor, LLC

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HGTG27N120BN

ON Semiconductor, LLC

TO-247

HGTG30N60B3

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HGTG30N60A4D

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